

Abstract of the Disclosure

A process chamber of semiconductor fabrication equipment includes a vessel in which a process gas is supplied, an upper electrode installed in an upper part of the vessel and to which power is applied, a shield ring extending alongside the upper electrode for insulating the upper electrode, a lower electrode disposed under the upper electrode as spaced from the upper electrode and to which power is applied to convert the process gas to plasma, an electrostatic chuck situated on the lower electrode and on which a wafer is received, and an insulation ring unit extending alongside the lower electrode for insulating the lower electrode. The shield ring and the insulation ring unit have a protection layer as an outer coating to prevent the shield ring and the insulation ring unit from being etched.